1. A method comprising:

developing a patterned photoresist;

applying a plasticizer to the surface of said patterned photoresist to decrease line edge roughness; and

reflowing the photoresist after applying the plasticizer.

2. The method of claim 1 including applying the plasticizer in a supercritical fluid.

3. The method of claim 2 including applying the plasticizer in a supercritical carbon dioxide fluid.

4. The method of claim 1 including applying the plasticizer as a separate step after developing the photoresist.

5. The method of claim 1 including applying the plasticizer with the developer.

6. The method of claim 1 including applying the plasticizer with the develop rinse.

7. The method of claim 1 including applying a plasticizer that improves the etch resistance of the photoresist.

8. The method of claim 1 wherein applying a plasticizer includes diffusing a plasticizer into the photoresist.

9. The method of claim 8 including diffusing a plasticizer in a vapor phase into the photoresist.

10. The method of claim 1 including controlling the amount of reflow by volatilizing the plasticizer during reflow.

11. The method of claim 1 including applying the plasticizer in liquid carbon dioxide.

12. The method of claim 1 including controlling the amount of reflow by cooling the photoresist.

13. A semiconductor structure comprising:
a patterned photoresist; and
a coating of plasticizer on said photoresist.

14. The structure of claim 13 wherein said photoresist is developed.

15. The structure of claim 13 wherein said plasticizer includes hydrofluoroether.

16. A method comprising:

applying a plasticizer to the surface of patterned photoresists to decrease line edge roughness; and

heating the photoresist and the applied plasticizer to reflow the photoresist.

17. The method of claim 16 including applying the plasticizer in a supercritical fluid.

18. The method of claim 17 including applying the plasticizer in a supercritical carbon dioxide fluid.

19. The method of claim 16 including applying the plasticizer as a separate step after developing the photoresist.

20. The method of claim 16 including applying the plasticizer with the developer.

21. The method of claim 16 including applying the plasticizer with the develop rinse.

22. The method of claim 16 including applying a plasticizer that improves the etch resistance of the photoresist.

23. The method of claim 16 wherein applying a plasticizer includes diffusing a plasticizer into the photoresist.

24. The method of claim 16 including controlling the amount of reflow by volatilizing the plasticizer during reflow.

25. The method of claim 16 including controlling the amount of reflow by cooling the photoresist.

26. The method of claim 16 including diffusing a plasticizer in a vapor phase into the photoresist.

27. The method of claim 16 including applying the plasticizer in liquid carbon dioxide.